

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N914

1N4148

SILICON SWITCHING DIODE

JEDEC D0-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N914, 1N4148 Silicon Planar Epitaxial Diode is characterized by its miniature size, ultra fast switching speed, low capacitance, low leakage, and high conductance. Accordingly, it is ideally suited for applications such as pulse applications, avalanche circuits, core drivers, and for any critical circuit requiring high conductance at power dissipation without sacrificing fast recovery capability. (Both devices have identical electrical and mechanical specifications.)

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL		UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Peak Working Reverse Voltage	V_{RWM}	75	V
Average Forward Current	I_O	150	mA
Forward Steady-State Current	I_F	200	mA
Peak Forward Surge Current (1.0 μs pulse)	I_{FSM}	2000	mA
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
BVR	$I_R=1.0\text{mA}$	100		V
BVR	$I_R=100\mu\text{A}$	75		V
I_R	$V_R=20\text{V}$		25	nA
V_F	$I_F=10\text{mA}$		1.0	V
C_T	$V_R=0\text{V}$, $f=1.0\text{MHz}$		4.0	pF
t_{rr}	$V_R=6.0\text{V}$, $I_F=10\text{mA}$, $I_{RR}=1.0\text{mA}$, $R_L=100\Omega$		4.0	ns